Docket No.: 50432-616 **PATENT**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	Customer Number: 20277
Seung-Hyun RHEE, et al.	:	Confirmation Number:
Serial No.:	:	Group Art Unit:
Filed: December 08, 2003	:	Examiner: Unknown

For: A METHOD OF FORMING AN INTERLEVEL DIELECTRIC LAYER EMPLOYING DIELECTRIC ETCH-BACK PROCESS WITHOUT EXTRA MASK SET

INFORMATION DISCLOSURE STATEMENT

Mail Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

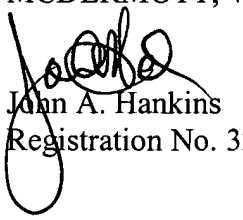
This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Serial No.:

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



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INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(PTO-1449)

ATTY. DOCKET NO.	SERIAL NO.
50432-616	
APPLICANT: **Seung-Hyun RHEE, et al.**	
FILING DATE: **December 08, 2003**	GROUP

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code2 (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US			
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code3 -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		Vincent ARNAL et al. "A Novel SiO_2-Air Low K for Copper Dual Damascene Interconnect", Conference Proceedings ULSI XVI (2001) Materials Research Society pp. 71-77.	
		B. SHIEH et al., "Air-Gap Formation During IMD Deposition to Lower Interconnect Capacitance", IEEE Electron Device Letters, Vol. 19, No. 1, January 1998	
		B. P. SHIEH et al., "Integration and Reliability Issues for Low Capacitance Air-Gap Interconnect Structures", 1998 IEEE	
		Vincent Arnal et al., "Optimization of CVD Dielectric Process to Achieve Reliable Ultra Low-*k* Air Gaps", Microelectronic Engineering 60 (2002) pp. 143-148	

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.